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(57) Abstract :

The present invention discloses a multi-layered structure (100) for an electronic device. The multi-layered structure (100) includes a substrate (102), a first sandwich layer (104), and a second sandwich layered (110). The first sandwich layer (10) is deposited over the substrate (102), and the first sandwich layer (104) includes a first insulating layer (106) deposited between a first (108-1) and a second conductive layer (108-2). Further, the second sandwich layer (110) is deposited over the first sandwich layer (104), and the second sandwich layer (110) includes a second insulating layer (112) deposited between a first (114-1) and a second semiconductor layer (114-2). Furthermore, the first insulating layer (104) is configured to prevent short circuits between the first (108-1) and second conductive layers (108-1), and the first (114-1) and second semiconductor layers (114-2) are configured to create an active layer for the electronic device.

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